

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Satish Athavale et al.

Serial No.: 09/757,123

Filed: January 9, 2001

Entitled: Method For Dry Etching Deep Trenches In A
Substrate

Group Art Unit: 1765

Examiner: C. BROWN

Docket No.: 01 P 7408 US

Batch No.: TBD

LETTER TO OFFICIAL DRAFTSMAN

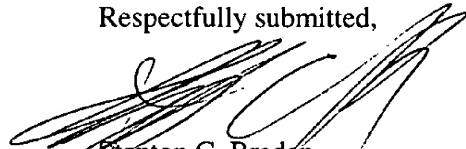
Attention: Drawing Processing Branch
Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Pursuant to M.P.E.P. Section 608.02, enclosed please find five (5) sheets of formal drawings in the referenced case. These are formal versions of the informal drawings filed with the application.

If there are any informalities with these drawings, Applicant requests issuance of a Form PTO-948 identifying the informalities noted by the Official Draftsman.

Respectfully submitted,


Stanton C. Braden
Reg. No. 32,556

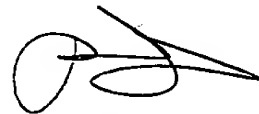
Date: February 12, 2002

Infineon Technologies North America Corp.
c/o Siemens Corporation
Intellectual Property Department
186 Wood Avenue South
Iselin, NJ 08830
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SCB/vl

CERTIFICATE OF MAILING PURSUANT TO 37 CFR § 1.8

I hereby certify that this correspondence is being deposited on or before the date, February 12, 2002 with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231

Date of Signature: February 12, 2002



Pamela J. Gewirtz

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